Robin John Nicholas

List of Publications by Year
in descending order

319	15,431	29994 54	20900 115
papers	citations	h-index	g-index

320	320	320	14546
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Direct measurement of the exciton binding energy and effective masses for charge carriers in organicâ€“inorganic tri-halide perovskites. Nature Physics, 2015, 11, 582-587.	6.5	1,651
2	Carbon Nanotube/Polymer Composites as a Highly Stable Hole Collection Layer in Perovskite Solar Cells. Nano Letters, 2014, 14, 5561-5568.	4.5	1,073
3	Low-Temperature Processed Electron Collection Layers of Graphene/TiO₂ Nanocomposites in Thin Film Perovskite Solar Cells. Nano Letters, 2014, 14, 724-730.	4.5	999
4	Highly selective dispersion of single-walled carbon nanotubes using aromatic polymers. Nature Nanotechnology, 2007, 2, 640-646.	15.6	988
5	Determination of the exciton binding energy and effective masses for methylammonium and formamidinium lead tri-halide perovskite semiconductors. Energy and Environmental Science, 2016, 9, 962-970.	15.6	603
6	Efficient perovskite solar cells by metal ion doping. Energy and Environmental Science, 2016, 9, 2892-2901.	15.6	372
7	A low viscosity, low boiling point, clean solvent system for the rapid crystallisation of highly specular perovskite films. Energy and Environmental Science, 2017, 10, 145-152.	15.6	319
8	Polymer Structure and Solvent Effects on the Selective Dispersion of Single-Walled Carbon Nanotubes. Journal of the American Chemical Society, 2008, 130, 3543-3553.	6.6	287
9	Structured Organicâ€“Inorganic Perovskite toward a Distributed Feedback Laser. Advanced Materials, 2016, 28, 923-929.	11.1	257
10	Exchange enhancement of the spin splitting in a GaAs-GaxAl1â^'xAs heterojunction. Physical Review B, 1988, 37, 1294-1302.	1.1	252
11	Diameter-selective encapsulation of metallocenes in single-walled carbon nanotubes. Nature Materials, 2005, 4, 481-485.	13.3	245
12	Magneto-optics in GaAs-Ga1â^'xAlxAs quantum wells. Physical Review B, 1986, 34, 4002-4009.	1.1	222
13	Observation of magnetic excitons and spin waves in activation studies of a two-dimensional electron gas. Physical Review B, 1990, 41, 1129-1134.	1.1	183
14	Measurements of the effective mass and scattering times of composite fermions from magnetotransport analysis. Physical Review Letters, 1994, 72, 1906-1909.	2.9	169
15	Enhanced Hole Extraction in Perovskite Solar Cells Through Carbon Nanotubes. Journal of Physical Chemistry Letters, 2014, 5, 4207-4212.	2.1	156
16	UVâ€“vis absorption spectroscopy of carbon nanotubes: Relationship between the Ï€-electron plasmon and nanotube diameter. Chemical Physics Letters, 2010, 493, 19-23.	1.2	155
17	Unraveling the Exciton Binding Energy and the Dielectric Constant in Single-Crystal Methylammonium Lead Triiodide Perovskite. Journal of Physical Chemistry Letters, 2017, 8, 1851-1855.	2.1	152
18	Structural and Optical Properties of Cs₂AgBiBr₆ Double Perovskite. ACS Energy Letters, 2019, 4, 299-305.	8.8	146

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19	Modification of the Electron-Phonon Interactions in GaAs-GaAlAs Heterojunctions. Physical Review Letters, 1987, 58, 77-80.	2.9	144
20	An experimental determination of the effective masses for GaxIn1â^'xAsyP1â^'yalloys grown on InP. Applied Physics Letters, 1979, 34, 492-494.	1.5	133
21	Research Update: Strategies for improving the stability of perovskite solar cells. APL Materials, 2016, 4, .	2.2	126
22	Extreme sensitivity of graphene photoconductivity to environmental gases. Nature Communications, 2012, 3, 1228.	5.8	120
23	Cyclotron resonance studies on bulk and two-dimensional conduction electrons in InSe. Solid State Communications, 1982, 44, 379-383.	0.9	111
24	Carbon Nanotubes in Perovskite Solar Cells. Advanced Energy Materials, 2017, 7, 1601839.	10.2	107
25	Investigating the Role of 4â€Tert Butylpyridine in Perovskite Solar Cells. Advanced Energy Materials, 2017, 7, 1601079.	10.2	106
26	Comparative studies on acid and thermal based selective purification of HiPCO produced single-walled carbon nanotubes. Chemical Physics Letters, 2004, 386, 239-243.	1.2	95
27	A study of the conduction band non-parabolicity, anisotropy and spin splitting in GaAs and InP. Semiconductor Science and Technology, 1987, 2, 568-577.	1.0	92
28	The magnetophonon effect. Progress in Quantum Electronics, 1985, 10, 1-75.	3.5	90
29	Noncovalent Binding of Carbon Nanotubes by Porphyrin Oligomers. Angewandte Chemie - International Edition, 2011, 50, 2313-2316.	7.2	90
30	Frequency-Shifted Polaron Coupling inGa0.47In0.53As Heterojunctions. Physical Review Letters, 1985, 55, 883-886.	2.9	89
31	Intersubband resonant scattering in GaAs-Ga1â^'xAlxAs heterojunctions. Physical Review B, 1992, 46, 12439-12447.	1.1	87
32	Cyclotron resonance and the magnetophonon effect in GaxIn1â^'xAsyP1â^'y. Applied Physics Letters, 1980, 37, 178-180.	1.5	84
33	Growth of GaSb by MOVPE. Semiconductor Science and Technology, 1988, 3, 315-320.	1.0	81
34	Ultrafast Charge Separation at a Polymerâ^'Single-Walled Carbon Nanotube Molecular Junction. Nano Letters, 2011, 11, 66-72.	4.5	81
35	The k.p interaction in InP and GaAs from the band-gap dependence of the effective mass. Journal of Physics C: Solid State Physics, 1984, 17, 4429-4442.	1.5	78
36	Observation of a Type II Heterojunction in a Highly Ordered Polymerâ^'Carbon Nanotube Nanohybrid Structure. Nano Letters, 2009, 9, 3871-3876.	4.5	77

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37	Two-dimensional spin confinement in strained-layer quantum wells. Physical Review B, 1990, 42, 9237-9240.	1.1	74
38	A study of the deep acceptor levels of iron in InP. Journal of Physics C: Solid State Physics, 1979, 12, 5145-5155.	1.5	73
39	Dopant-Free Planar nâ€“iâ€“p Perovskite Solar Cells with Steady-State Efficiencies Exceeding 18%. ACS Energy Letters, 2017, 2, 622-628.	8.8	73
40	Cyclotron-resonance study of nonparabolicity and screening in GaAs-Ga1â^'xAlxAs heterojunctions. Physical Review B, 1987, 36, 4789-4795.	1.1	71
41	Photoluminescence of GaSb grown by metal-organic vapour phase epitaxy. Semiconductor Science and Technology, 1991, 6, 45-53.	1.0	70
42	Quantum transport in GaInAs-AlInAs heterojunctions, and the influence of intersubband scattering. Solid State Communications, 1982, 43, 907-911.	0.9	66
43	Odd and even fractionally quantized states in GaAs-GaAlAs heterojunctions. Surface Science, 1986, 170, 141-147.	0.8	66
44	Carrier-concentation-dependent electronâ€“LO-phonon coupling observed in GaAs-(Ga,Al)As heterojunctions by resonant-polaron cyclotron resonance. Physical Review B, 1988, 38, 13133-13142.	1.1	65
45	The Impact of Phase Retention on the Structural and Optoelectronic Properties of Metal Halide Perovskites. Advanced Materials, 2016, 28, 10757-10763.	11.1	65
46	An experimental determination of enhanced electron g-factors in GaInAs-A1InAs heterojunctions. Solid State Communications, 1983, 45, 911-914.	0.9	63
47	Controlled orientation of ellipsoidal fullerene C70 in carbon nanotubes. Applied Physics Letters, 2004, 84, 792-794.	1.5	63
48	First observation of the quantum Hall effect in a Ga0.47In0.53Asâ€‰nP heterostructure with three electric subbands. Applied Physics Letters, 1986, 48, 712-714.	1.5	59
49	Î“-Xmixing in the miniband structure of a GaAs/AlAs superlattice. Physical Review Letters, 1989, 63, 2284-2287.	2.9	59
50	Chirality Assignment of Single-Walled Carbon Nanotubes with Strain. Physical Review Letters, 2004, 93, 156104.	2.9	59
51	Optically detected cyclotron resonance of GaAs quantum wells: Effective-mass measurements and offset effects. Physical Review B, 1992, 46, 13394-13399.	1.1	58
52	Direct spectroscopic evidence of energy transfer from photo-excited semiconducting polymers to single-walled carbon nanotubes. Nanotechnology, 2008, 19, 095603.	1.3	56
53	Evidence for Anderson localisation in Landau level tails from the analysis of two-dimensional Shubnikovâ€”de Haas conductivity minima. Solid State Communications, 1977, 23, 341-345.	0.9	55
54	Fractional quantum Hall effect in tilted magnetic fields. Physical Review B, 1987, 36, 4528-4530.	1.1	55

#	Article	IF	Citations
55	Highly Crystalline Methylammonium Lead Tribromide Perovskite Films for Efficient Photovoltaic Devices. ACS Energy Letters, 2018, 3, 1233-1240.	8.8	54
56	The effects of nitrogen and boron doping on the optical emission and diameters of single-walled carbon nanotubes. Carbon, 2006, 44, 2752-2757.	5.4	53
57	Magnetotransport in a pseudomorphic GaAs/Ga0.8In0.2As/Ga0.75Al0.25As heterostructure with a Si Î´-doping layer. Physical Review B, 1995, 52, 12218-12231.	1.1	52
58	Electronic and Mechanical Modification of Single-Walled Carbon Nanotubes by Binding to Porphyrin Oligomers. ACS Nano, 2011, 5, 2307-2315.	7.3	50
59	GaSb heterostructures grown by MOVPE. Journal of Crystal Growth, 1988, 93, 70-78.	0.7	49
60	Carrier-concentration-dependent polaron cyclotron resonance in GaAs heterostructures. Physical Review B, 1992, 45, 4296-4300.	1.1	49
61	Comparative study of photoluminescence of single-walled carbon nanotubes wrapped with sodium dodecyl sulfate, surfactin and polyvinylpyrrolidone. Nanotechnology, 2005, 16, S202-S205.	1.3	49
62	New phases of the 2D electron system in the ultra-quantum limit observed by cyclotron resonances. Physical Review Letters, 1993, 70, 2150-2153.	2.9	48
63	Anomalies in the cyclotron resonance in high-mobility GaAs-Ga1â^'xAlxAs heterojunctions. Physical Review B, 1989, 39, 10955-10962.	1.1	47
64	Observation of optically detected magnetophonon resonance. Physical Review Letters, 1991, 66, 794-797.	2.9	47
65	Rapid epitaxy-free graphene synthesis on silicidated polycrystalline platinum. Nature Communications, 2015, 6, 7536.	5.8	46
66	Two-dimensional magnetophonon resonance. I. GaInAs-InP superlattices. Journal of Physics C: Solid State Physics, 1983, 16, L573-L578.	1.5	45
67	Effect masses and non-parabolicity in GaxIn1-xAs. Journal of Physics C: Solid State Physics, 1985, 18, 2667-2676.	1.5	45
68	Wavelength-dependent photoconduction effects on the second sub-band occupancy in (Al, Ga)As/GaAs heterojunctions. Semiconductor Science and Technology, 1987, 2, 783-789.	1.0	45
69	Cyclotron phonon emission and electron energy loss rates in GaAs-GaAlAs heterojunctions. Semiconductor Science and Technology, 1989, 4, 879-884.	1.0	45
70	Raman scattering in InP1-xAsxalloys. Journal of Physics C: Solid State Physics, 1980, 13, 899-910.	1.5	44
71	Spatially resolved studies of the phases and morphology of methylammonium and formamidinium lead tri-halide perovskites. Nanoscale, 2017, 9, 3222-3230.	2.8	44
72	Experimental studies of thev=15hierarchy in the fractional quantum Hall effect. Physical Review B, 1988, 38, 2200-2203.	1.1	43

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73	Observation of decoupled heavy and light holes in GaAs-Ga1â^'xAlxAs quantum wells by magnetoreflectivity. Physical Review B, 1988, 38, 1323-1329.	1.1	42
74	Cyclotron resonance of electrons in a narrow GaAs/(Ga,Al)As quantum well: Polaron effects and non-parabolicity. Surface Science, 1988, 196, 429-436.	0.8	41
75	Thiophene-based dyes for probing membranes. Organic and Biomolecular Chemistry, 2015, 13, 3792-3802.	1.5	41
76	Giant Fine Structure Splitting of the Bright Exciton in a Bulk MAPbBr₃ Single Crystal. Nano Letters, 2019, 19, 7054-7061.	4.5	41
77	Two-dimensional magnetophonon resonance. II. GaInAs-AlInAs heterojunctions. Journal of Physics C: Solid State Physics, 1983, 16, L579-L584.	1.5	39
78	Growth of InAs/GaSb strained layer superlattices. I. Journal of Crystal Growth, 1994, 145, 778-785.	0.7	39
79	Effective mass and quantum lifetime in a Si/Si0.87Ge0.13/Si twoâ€dimensional hole gas. Applied Physics Letters, 1994, 64, 357-359.	1.5	37
80	Temperature induced restoration of fluorescence from oxidised single-walled carbon nanotubes in aqueous sodium dodecylsulfate solution. Physical Chemistry Chemical Physics, 2006, 8, 3547.	1.3	37
81	Terahertz Excitonic Response of Isolated Single-Walled Carbon Nanotubes. Journal of Physical Chemistry C, 2009, 113, 18106-18109.	1.5	36
82	Nanoengineering Coaxial Carbon Nanotubeâ€"Dual-Polymer Heterostructures. ACS Nano, 2012, 6, 6058-6066.	7.3	36
83	An ultrafast carbon nanotube terahertz polarisation modulator. Journal of Applied Physics, 2014, 115, .	1.1	36
84	Impact of microstructure on the electronâ€"hole interaction in lead halide perovskites. Energy and Environmental Science, 2017, 10, 1358-1366.	15.6	36
85	An investigation of the valley splitting in n-channel silicon ã€^100ã€‰ inversion layers. Solid State Communications, 1980, 34, 51-55.	0.9	35
86	Quantum oscillations at a Ga0.47In0.53Asî—¸InP heterojunction interface. Solid State Communications, 1982, 43, 825-828.	0.9	35
87	Influence of acoustic phonons on inter-subband scattering in GaAs-GaAlAs heterojunctions. Semiconductor Science and Technology, 1989, 4, 885-888.	1.0	35
88	GaSb/GaInSb quantum wells grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 1989, 54, 922-924.	1.5	35
89	Title is missing!. Journal of Physics C: Solid State Physics, 1986, 19, 77-92.	1.5	34
90	Novel Carbon Nanotubeâ€Conjugated Polymer Nanohybrids Produced By Multiple Polymer Processing. Advanced Materials, 2013, 25, 4365-4371.	11.1	34

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91	Cyclotron resonance and polaron effects in a two-dimensional electron gas in GaInAs. Surface Science, 1984, 142, 380-387.	0.8	33
92	Phonon drag contribution to thermoelectric power in two-dimensional systems. Journal of Physics C: Solid State Physics, 1985, 18, L695-L698.	1.5	33
93	Subband-Landau level coupling in a two-dimensional electron gas in tilted magnetic fields. Journal of Physics C: Solid State Physics, 1986, 19, L107-L112.	1.5	33
94	Cyclotron resonance and screening effects in GaAs-GaAlAs heterojunctions. Superlattices and Microstructures, 1986, 2, 319-322.	1.4	33
95	Chirality-dependent boron-mediated growth of nitrogen-doped single-walled carbon nanotubes. Physical Review B, 2005, 72, .	1.1	33
96	Two-dimensional magnetophonon resonance in GaInAs-InP and GaInAs-AlInAs heterojunctions and superlattices. Surface Science, 1984, 142, 368-374.	0.8	32
97	Temperature dependence of the cyclotron-resonance linewidth in GaAs-Ga1â^'xAlxAs heterojunctions. Physical Review B, 1989, 39, 13302-13309.	1.1	32
98	Strain reconstruction of the valence band in Ga1 â^' xInxSb/GaSb quantum wells. Surface Science, 1990, 228, 270-274.	0.8	32
99	Evidence for a reduction in the momentum matrix element P2due to alloy disorder in InAp1-xPx. Journal of Physics C: Solid State Physics, 1979, 12, 1641-1651.	1.5	31
100	Solubilization of Carbon Nanotubes with Ethylene-Vinyl Acetate for Solution-Processed Conductive Films and Charge Extraction Layers in Perovskite Solar Cells. ACS Applied Materials & Interfaces, 2019, 11, 1185-1191.	4.0	31
101	GaAs/GaSb strainedâ€layer heterostructures deposited by metalorganic vapor phase epitaxy. Applied Physics Letters, 1989, 54, 1241-1243.	1.5	30
102	On the Electronicg-Faetor in n-Type Silicon Inversion Layers. Physica Status Solidi (B): Basic Research, 1980, 99, 237-242.	0.7	29
103	Competition between LO and TO phonon scattering in GaAs/GaAlAs heterojunctions. Surface Science, 1988, 196, 451-458.	0.8	28
104	Enhanced carrier densities and device performance in piezoelectric pseudomorphic highâ€electron mobility transistor structures. Applied Physics Letters, 1992, 61, 1072-1074.	1.5	27
105	Growth of strained layer superlattices. II. Journal of Crystal Growth, 1995, 146, 495-502.	0.7	27
106	Magnetic separation of Fe catalyst from single-walled carbon nanotubes in an aqueous surfactant solution. Carbon, 2005, 43, 1151-1155.	5.4	27
107	Energy relaxation mechanisms in n-type GaAs from magnetophonon spectroscopy. Journal of Physics C: Solid State Physics, 1976, 9, 1253-1262.	1.5	26
108	The electric sub-band structure of electron accumulation layers in InSe from Shubnikov-de Haas oscillations and inter-sub-band resonance. Journal of Physics C: Solid State Physics, 1983, 16, 4285-4295.	1.5	26

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109	Cyclotron resonance in InAs/GaSb heterostructures. Semiconductor Science and Technology, 1992, 7, 985-993.	1.0	26
110	Interface studies of InAs/GaSb superlattices by Raman scattering. Surface Science, 1992, 267, 176-180.	0.8	26
111	Influence of light on the confinement potential of GaAs/AlxGa1â^'xAs heterojunctions. Physical Review B, 1995, 52, 2688-2696.	1.1	26
112	Metal-Insulator Oscillations in a Two-Dimensional Electron-Hole System. Physical Review Letters, 2000, 85, 2364-2367.	2.9	26
113	Inter-subband scattering rates in GaAs-GaAlAs heterojunctions. Semiconductor Science and Technology, 1990, 5, 1081-1087.	1.0	25
114	Introduction. Carbon-based electronics: fundamentals and device applications. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2008, 366, 189-193.	1.6	25
115	Resonant 2D magnetopolarons in accumulation layers on n-Hg0.8Cd0.2Te. Solid State Communications, 1986, 58, 833-838.	0.9	24
116	An optically detected cyclotron resonance study of bulk GaAs. Semiconductor Science and Technology, 1994, 9, 198-206.	1.0	24
117	MOVPE grown self-assembled and self-ordered InSb quantum dots in a GaSb matrix assessed by AFM, CTEM, HRTEM and PL. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 80, 112-115.	1.7	24
118	Production of Highâ€Purity Singleâ€Chirality Carbon Nanotube Hybrids by Selective Polymer Exchange. Small, 2013, 9, 2245-2249.	5.2	24
119	Evidence for a contribution to the extrinsic photoconductive signal by hopping through excited states of the donors in silicon and CdTe. Solid State Communications, 1977, 24, 55-60.	0.9	23
120	Two-dimensional behaviour due to electrons bound at defects in InSe. Surface Science, 1982, 113, 339-346.	0.8	23
121	Pressure dependence of light-hole transport in strained InGaAs/GaAs. Surface Science, 1990, 229, 122-125.	0.8	23
122	High-pressure investigation of GaSb andGa1â^'xInxSb/GaSb quantum wells. Physical Review B, 1991, 43, 4994-5000.	1.1	23
123	Collapse of High Field Magnetophonon Resonance in GaAs-GaAlAs Heterojunctions. Physical Review Letters, 1994, 73, 589-592.	2.9	23
124	Observation of magnetic-field-induced semimetal-semiconductor transitions in crossed-gap superlattices by cyclotron resonance. Physical Review B, 1994, 49, 10474-10483.	1.1	23
125	The analysis of thermal activation of two-dimensional Shubnikov-De Haas conductivity minima and maxima. Surface Science, 1978, 73, 106-115.	0.8	22
126	The magnetophonon effect in InAs1-xPx. Journal of Physics C: Solid State Physics, 1979, 12, 1653-1664.	1.5	22

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127	Cyclotron resonance linewidth in a two-dimensional electron gas. Surface Science, 1982, 113, 326-332.	0.8	22
128	Oscillatory behavior in the photoluminescence excitation and photoconductivity spectra of GaAs-AlAs superlattices. Physical Review B, 1989, 39, 1219-1223.	1.1	22
129	Devices and desires in the 2-4 mu m region based on antimony-containing III-V heterostructures grown by MOVPE. Semiconductor Science and Technology, 1993, 8, S380-S385.	1.0	22
130	[001]- and piezoelectric-[111]-oriented InAs/GaSb structures under hydrostatic pressure. Physical Review B, 1994, 49, 16614-16621.	1.1	22
131	Limits on band discontinuities in GaAs-GaAlAs heterostructures deduced from optical photoresponse. Journal of Physics C: Solid State Physics, 1985, 18, L891-L896.	1.5	21
132	GaSb/InAs heterojunctions grown by MOVPE: Effect of gas switching sequences on interface quality. Journal of Crystal Growth, 1991, 110, 677-682.	0.7	21
133	High-field magnetoresistance in GaAs/Ga0.7Al0.3As heterojunctions arising from elastic and inelastic scattering. Physical Review B, 1993, 48, 5457-5468.	1.1	21
134	Surface-Effect-Induced Optical Bandgap Shrinkage in GaN Nanotubes. Nano Letters, 2015, 15, 4472-4476.	4.5	21
135	High field magneto-transport measurements in GaAs-GaAlAs multilayers. Surface Science, 1982, 113, 290-294.	0.8	20
136	Frequency shifted polaron coupling in GaInAs heterostructures. Surface Science, 1986, 170, 542-548.	0.8	20
137	Quantum transport in accumulation layers on Cd0.2Hg0.8Te. Journal of Physics C: Solid State Physics, 1986, 19, 35-42.	1.5	20
138	Persistent photoconductivity in Ga0.49In0.51P/GaAs heterojunctions. Journal of Applied Physics, 1989, 65, 2756-2760.	1.1	20
139	Cyclotron resonance of both magnetopolaron branches for polar and neutral optical phonon coupling in the layer compound InSe. Physical Review B, 1992, 45, 12144-12147.	1.1	20
140	High magnetic field studies of the crossed-gap superlattice system InAs/GaSb. Physica B: Condensed Matter, 1993, 184, 268-276.	1.3	20
141	Cyclotron resonance of high-mobility GaAs/AlGaAs (311) 2DHGs. Semiconductor Science and Technology, 1993, 8, 1465-1469.	1.0	20
142	Searches for skyrmions in the limit of zero -factor. Semiconductor Science and Technology, 1998, 13, 671-679.	1.0	20
143	Shallow donor spectroscopy and polaron coupling in Ga0.47In0.53As. Journal of Physics C: Solid State Physics, 1985, 18, L427-L431.	1.5	19
144	Hot carrier relaxation of Dirac fermions in bilayer epitaxial graphene. Journal of Physics Condensed Matter, 2015, 27, 164202.	0.7	19

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145	GaSb/InAs heterojunctions grown by MOVPE. Journal of Crystal Growth, 1991, 107, 422-427.	0.7	18
146	Magnetoconductivity in a mesoscopic antidot array. Physical Review B, 1993, 47, 7348-7353.	1.1	18
147	Optical and magnetotransport properties of semimetallic InAs/(In,Ga)Sb superlattices. Physica B: Condensed Matter, 1994, 201, 271-279.	1.3	18
148	Orientation and pressure dependence of the band overlap in InAs/GaSb structures. Semiconductor Science and Technology, 1994, 9, 118-122.	1.0	18
149	Improved photoluminescence from electrochemically passivated GaSb. Semiconductor Science and Technology, 1997, 12, 413-418.	1.0	18
150	Infrared single wavelength gas composition monitoring for metalorganic vapour-phase epitaxy. Journal of Crystal Growth, 2000, 221, 166-171.	0.7	18
151	The effects of high uniaxial stress on the far infra-red impurity spectra of high purity n- and p-type silicon. Solid State Communications, 1978, 26, 11-15.	0.9	17
152	Studies deep chromium acceptor levels in InP. Journal of Physics C: Solid State Physics, 1981, 14, 2135-2146.	1.5	17
153	Magneto-optical studies of GainAsî—¸InP quantum wells. Superlattices and Microstructures, 1987, 3, 471-475.	1.4	17
154	Evolution of the electronic states of coupled (In,Ga)As-GaAs quantum wells into superlattice minibands. Physical Review B, 1990, 42, 3024-3029.	1.1	17
155	Magnetotransport of piezoelectric [111] oriented strained quantum wells. Applied Physics Letters, 1991, 59, 659-661.	1.5	17
156	Electroluminescence out to 2.1 mu m observed in GaSb/InxGa1-xSb quantum wells grown by MOVPE. Semiconductor Science and Technology, 1994, 9, 87-90.	1.0	17
157	Miniband structure inInxGa1â^'xAs-GaAs strained-layer superlattices. Physical Review B, 1991, 43, 2246-2254.	1.1	16
158	Internal self-ordering in In(Sb,As), (In,Ga)Sb, and (Cd,Zn,Mn)Se nano-agglomerates/quantum dots. Applied Physics Letters, 2001, 79, 946-948.	1.5	16
159	High magnetic field studies of the twoâ€dimensional electron gas in GaInAsâ€InP superlattices. Applied Physics Letters, 1983, 43, 293-295.	1.5	15
160	Structural and electronic properties of PbTe/Pb1â^'xSnxTe superlattices. Surface Science, 1984, 142, 571-578.	0.8	15
161	Measurements of hot electron magnetophonon resonance in GaAs/GaAlAs heterostructures. Solid-State Electronics, 1988, 31, 781-784.	0.8	15
162	Piezoelectric control of doping and band structure in the crossed gap system GaSb/InAs. Surface Science, 1992, 263, 575-579.	0.8	15

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163	Piezoelectric effects in superlattices. Semiconductor Science and Technology, 1993, 8, S367-S372.	1.0	15
164	Temperature dependence of the band overlap in InAs/GaSb structures. Physical Review B, 1995, 51, 1729-1734.	1.1	15
165	Bandgap-selective chemical doping of semiconducting single-walled carbon nanotubes. Nanotechnology, 2004, 15, 1844-1847.	1.3	15
166	Hyperspectral Imaging of Exciton Photoluminescence in Individual Carbon Nanotubes Controlled by High Magnetic Fields. Nano Letters, 2014, 14, 5194-5200.	4.5	15
167	Thermoelectric power of GaAs-GaAlAs heterostructures in high magnetic fields. Solid State Communications, 1986, 57, 381-384.	0.9	14
168	A study of parallel-field magnetoresistance of accumulation layers at anodic oxide films on n-(Hg,) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 654-663.	1.0	14
169	The pressure dependence of the effective mass in a GaAs/AlGaAs heterojunction. Semiconductor Science and Technology, 1992, 7, 787-792.	1.0	14
170	A magneto-optical study of coupled quantum wells in strained GaInSb/GaSb. Physica B: Condensed Matter, 1993, 184, 106-110.	1.3	14
171	â€œIntrinsicâ€•quantum Hall effect in InAs/Ga1â^'xInxSb crossed gap heterostructures in high magnetic fields. Surface Science, 1994, 305, 156-160.	0.8	14
172	A modified phenomenological description of the exchange interactions in dilute magnetic semiconductors. Semiconductor Science and Technology, 1995, 10, 791-796.	1.0	14
173	Cyclotron resonance of electrons and holes in graphene monolayers. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2008, 366, 237-243.	1.6	14
174	Electron concentration dependent fractional quantisation in a two dimensional system. Solid State Communications, 1985, 56, 173-176.	0.9	13
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